

**Notice of References Cited**

Application/Control No.

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Applicant(s)/Patent Under  
Reexamination  
ANTHONY ET AL.

Examiner

Anh D. Mai

Art Unit

2814

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*		Document Number	Date	Name	Classification	
		Country Code-Number-Kind Code	MM-YYYY			
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	B	US- -				
	C	US- -				
	D	US- -				
	E	US- -				
	F	US- -				
	G	US- -				
	H	US- -				
	I	US- -				
	J	US- -				
	K	US- -				
	L	US- -				
	M	US- -				

**FOREIGN PATENT DOCUMENTS**

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		Country Code-Number-Kind Code	MM-YYYY				
	N	- -					
	O	- -					
	P	- -					
	Q	- -					
	R	- -					
	S	- -					
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	W	Ghandhi S. VLSI Fabrication Principles. John Wiley & Sons, Inc. 1994, pp. 539-545.
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\*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)  
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.